

SANYO Semiconductors

DATA SHEET

Monolithic Digital IC

LB1231 Series — High-Voltage, Large Current Darlington Transistor Array

The circuit configuration of this IC is of 7-channel Darlington transistor array consisting of NPN transistors. It is especially suited for use in hammer drivers and lamp, relay drivers. It contains spark killer diodes against L load.

Features High-voltage (VCEO≥50V), large-current (ICmax=500mA) drive

LB1231 . Drivable by TTL, MOS output

LB1232 . Contains base current limiting resistors, Zener diodes for level shift.

. Direct drivable by 24V P MOS.

LB1233 . Contains base current limiting resistors.

. Direct drivable by TTL, C MOS output.

LB1234 . Contains base current limiting resistors.

. Direct drivable by C MOS, P MOS output.

Absolute Maximum Ratings at Ta=25°	C			unit
	VOUT		50	V
		Per unit	500	mΑ
Input Supply Voltage	V _{IN}	LB1232/33/34	30	V
Input Current	IIN	LB1231 only	25	mΑ
GND Pin Current	IGND	7ch simultaneously o	on, 2.8	A
		f=10Hz, duty,=23%		
Allowable Power Dissipation	$P_{\mathbf{d}}$ max		1.5	W
Operating Temperature	Topr		-20 to +75	°C
Storage Temperature	Tstg		-40 to +150	°C
Allowable Operating Conditions at	Ta=25°C			unit
Output Supply Voltage VouT			50	V
Input "H" Level Voltage VIH	LB1232	IOUT=350mA	11 to 30	V
	LB1233	IOUT=350mA	3 to 30	V
	LB1234	IOUT=350mA	5 to 30	V
Input "L" Level Voltage VIL	LB1231/3	33 I _{OUT} ≦100µA	-0.3 to $+0.3$	V
	LB1232	Ioυτ≤100μA	-0.3 to $+6.0$	V
	LB1234	IOUT≦100µA	-0.3 to +0.7	v

Package Dimensions 3064-D16TR

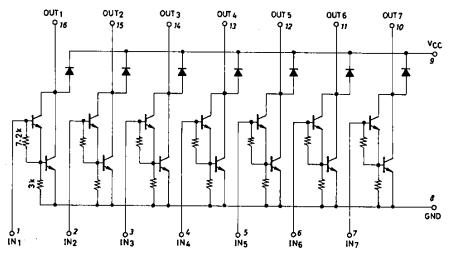
(unit: mm)

19.1 SANYO: DIP16

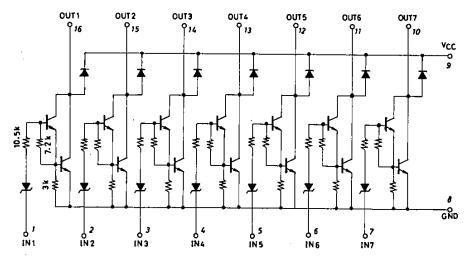
Electrical Characteristics	at Ta=25°	°C	min	typ	max	unit
Output Leak Current	IOFF	V _{OUT} =50V			100	ıιΑ
Output Voltage	v_{OH1}	$I_{IN}=0.25$ mA, $I_{OUT}=100$ mA		0.9	1.1	v
	v_{OH2}	$I_{IN}=0.35$ mA, $I_{OUT}=200$ mA		1.1	1.3	V
	v_{OH3}	I _{IN} =0.5mA, I _{OUT} =350mA		1.3	1.6	٧
	V _{OH4}	$I_{ ext{IN}}= ext{lmA}$, $I_{ ext{OUT}}= ext{400mA}$			2.4	V
Input Voltage	$\mathtt{v_{in}}$	LB1231 I _{IN} =1mA		1.35	1.7	v
Input Current	v_{IN}	LB1232 V _{IN} =17V		0.82	1.25	mΑ
		LB1233 V _{IN} =3.85V		0.93	1.35	mA
		LB1234 V _{IN} =5V		0.35	0.5	mA
		LB1234 V _{IN} =12V		1.00	1.45	mΑ
Spark Killer Diode Leak Currnet	IR(S)	$V_{R(S)}=50V$			100	Αιζ
Spark Killer Diode 🗀 😗	VF(S)l	$I_{F(S)} = 350 \text{mA}$			2.0	V
Forward Voltage	VF(S)2	$I_F(s) = 400 \text{mA}$			2.4	V

Equivalent Circuits LB1231

Unit (resistance: Ω)



LB1232

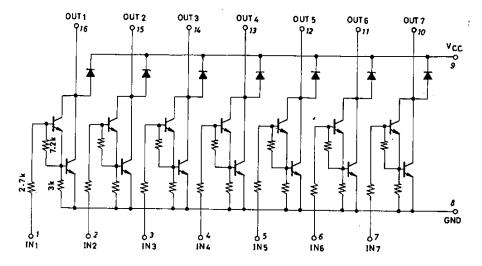


Continued on next page.

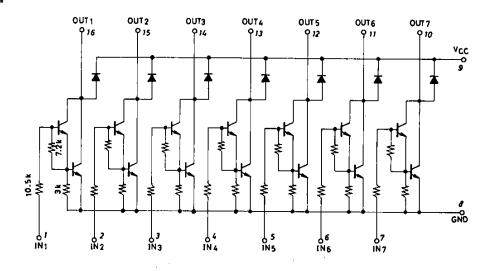
Continued from preceding page.

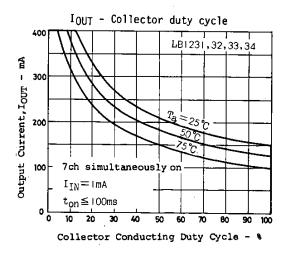
Unit (resistance: Ω)

LB1233



LB1234





- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
 - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use:
 - ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.